

SOD-882 封装

■ 特性

1. 符合RoHS与无卤要求
2. 低电容
3. 低限制电压
4. 低漏流
5. 满足 61000-4-2 (ESD) 15~20KV (air), 8~25KV (contact)



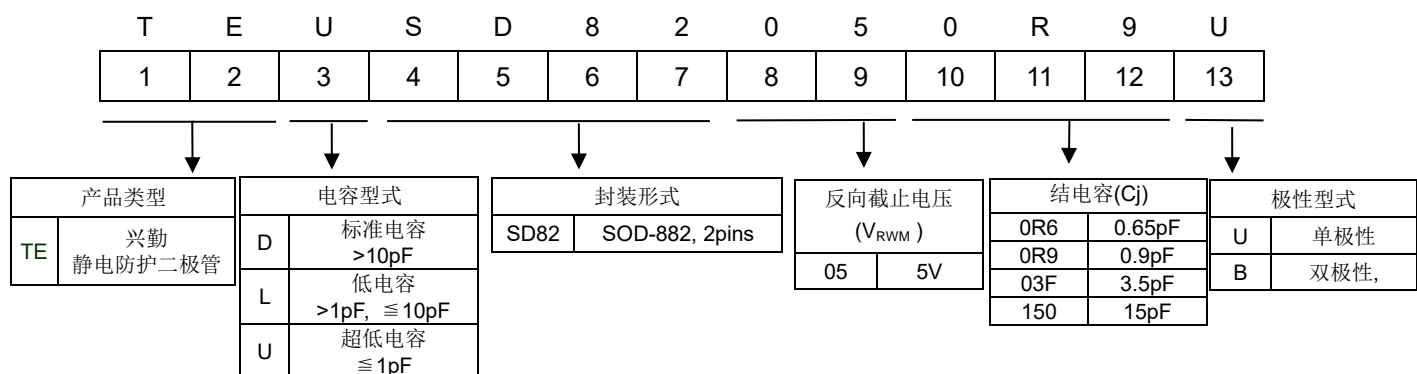
■ 用途

1. 手机与配件
2. 笔记本电脑, 服务器
3. PCI express, SATA, USB 2.0,DVI, 显示端口
4. 可携式装置

■ 机械数据

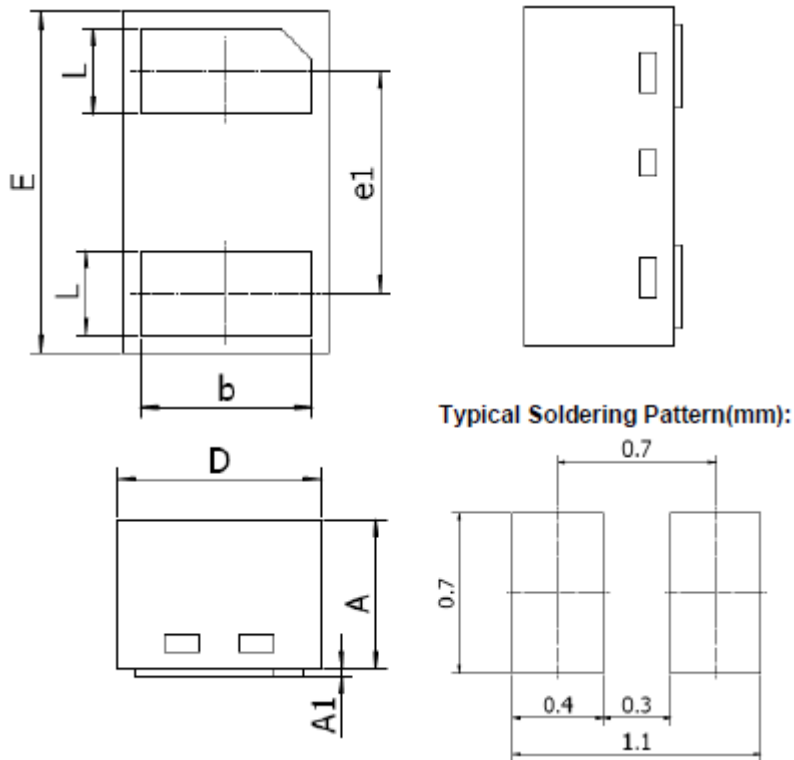
1. 封装型式:SOD-882, 封装塑料符合防火等级UL94-V0
2. 满足MSL level 1, per J-STD-020

■ 编码规则



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■ 结构与尺寸



单位: mm

Symbol	SOD-882	
	Min	Max
A	0.46	0.5
A1	-	0.03
b	0.45	0.55
D	0.55	0.65
E	0.95	1.05
e1	Typ.0.65	
L	0.2	0.3

■ 图标概要与配置



■ 电气特性 (T_A=25°C)

兴勤料号	最大反向截止电压	反向漏电流	产品极性 单/双向	印字	峰值脉冲功率	峰值脉冲电流	接触放电	空气放电	工作温度	存储温度
	V _{RWM} (V)	I _R (μ A)	Uni/Bi (单/双)		P _{PK} (W)	I _{PP} (A)	KV	KV	T _J (°C)	T _{stg} (°C)
	Max	Max								
TEUSD82050R6U	5	1	Uni	L		4	8	15	-55 to +150	-55 to +150
TEUSD82050R9U	5	1	Uni	N		1	8	15	-55 to +150	-55 to +150
TEUSD820503FU	5	1	Uni	Q5		3.5	12	15	-55 to +125	-55 to +150
TEDSD8205150U	5	0.5	Uni	C	60	5	25	20	-55 to +125	-55 to +150

■ 电气特性 (T_A=25°C)

TEUSD82050R6U						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	5.4			V	IT = 1mA
Reverse Leakage Current	I _R			1	uA	VR = VRWM
Clamping Voltage	V _C			20	V	IPP = 4A (8/20μs pulse)
Junction Capacitance	C _J		0.65		pF	VR = 0V, f = 1MHz

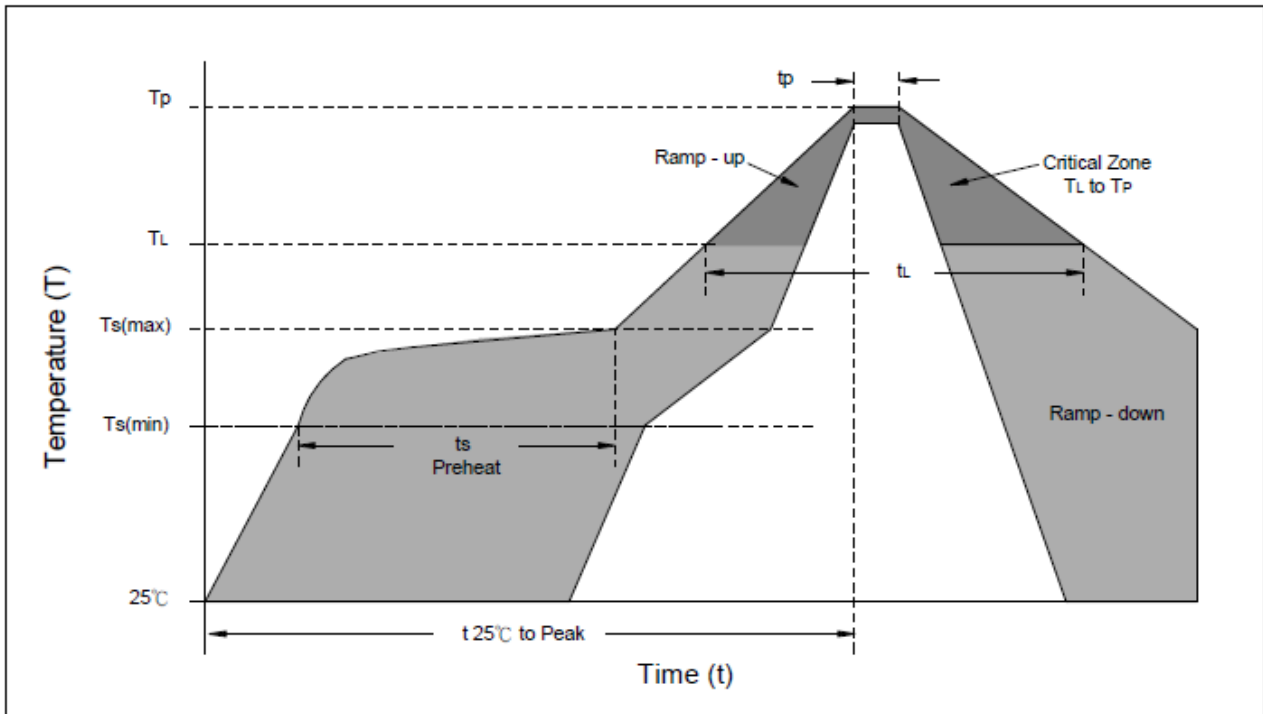
TEUSD82050R9U						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	5.4			V	IT = 1mA
Reverse Leakage Current	I _R			1	uA	VR = VRWM
Clamping Voltage	V _C			12.9	V	IPP = 1A (8/20μs pulse)
Junction Capacitance	C _J		0.9		pF	VR = 0V, f = 1MHz

TEUSD820503FU						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	5.6		11	V	IT = 1mA
Reverse Leakage Current	I _R			1	uA	VR = VRWM
Clamping Voltage	V _C			13	V	IPP = 3.5A (8/20μs pulse)
Junction Capacitance	C _J		3.5		pF	VR = 0V, f = 1MHz

TEDSD8205150U						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	5.6			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	nA	VR = VRWM
Clamping Voltage	V _C			12	V	IPP = 5A (8/20μs pulse)
Junction Capacitance	C _J		15		pF	VR = 0V, f = 1MHz

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■ 推荐焊接条件

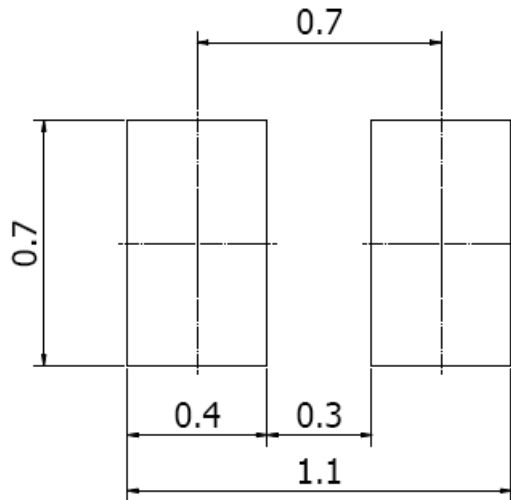


Reflow Condition	Lead-free assembly
Preheat -Temperature Min(Ts min) -Temperature Min(Ts max) -Time (min to max) (ts)	150°C 200°C 60 – 180 seconds
Average ramp up rate -Temperature Liquidus (TL) to peak	3°C/second max
Ts(max) to TL -Ramp-up Rate	3°C/second max.
Reflow -Temperature Liquidus (TL) -Time (tl)	217°C 60 – 150 seconds
Peak Temperature (TP)	260°C
Time within 5°C of actual peak Temperature(tp)	20 – 40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to peak Temperature(TP)	8 minutes max.
Do not exceed	260°C

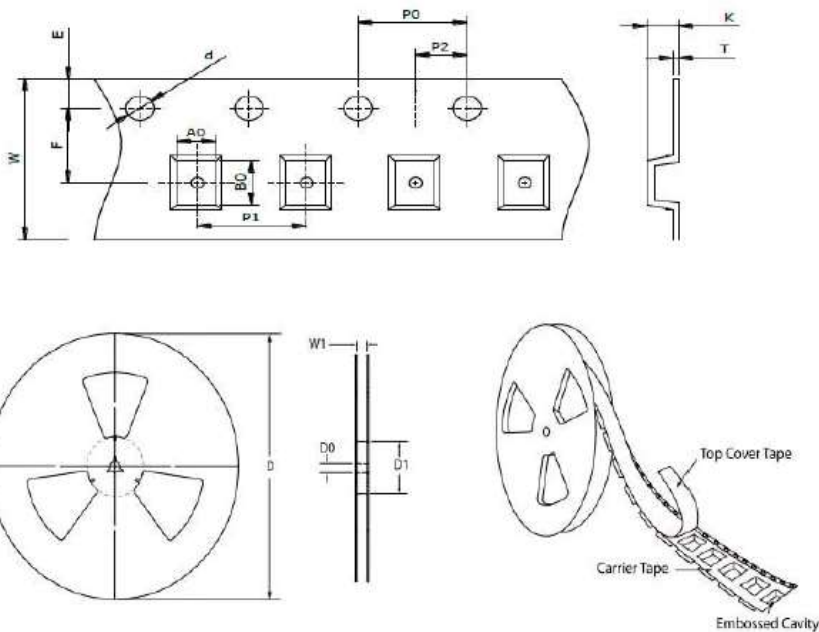
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■ 推荐焊盘尺寸

单位:mm



■ 包装



单位:mm

Symbol	DFN1006-2L
A0	0.67 ± 0.10
B0	1.12 ± 0.10
K	0.60 ± 0.10
d	1.50 ± 0.10
D	178.00 ± 2.00
D0	13.00 ± 0.20
D1	MIN. 54.00
E	1.75 ± 0.10
F	3.50 ± 0.10
P0	4.00 ± 0.10
P1	4.00 ± 0.10
P2	2.00 ± 0.10
T	0.22 ± 0.05
W	8.00 ± 0.20
W1	MAX. 13.50

静电防护二极管 :TE_xSD82 系列

SOD-882 封装



■ 数量

最小包装数量(MPQ): 10,000pcs

封装型式	卷盘尺寸(英寸)	单卷数量(Kpcs)
SOD-882	7"	10

■ 仓库存储条件

● 存储条件:

1. 储存温度: $-10^{\circ}\text{C} \sim +40^{\circ}\text{C}$
2. 相对湿度: $\leq 75\% \text{RH}$
3. 不要将本产品存放在有腐蚀性气体或是阳光直接照射的环境中保管

● 存储期限: 1 年